

| L Number | Hits | Search Text | DB | Time stamp |
|-------------|--------|--|---|---------------------|
| 3 | 3330 | (control near gate) and (source and drain) and memory and (ONO (oxide-nitride-oxide) (oxide/nitride/oxide) (silicon near oxide/silicon near nitride/silicon near oxide)) and (@ad<20030514 @rlad<20030514) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/21 13:49 |
| 4 | 533630 | ((insulat\$3 dielectric) near (layer film)) SOI (silicon near on near insulator) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/21 13:50 |
| 5 | 3048 | ((control near gate) and (source and drain) and memory and (ONO (oxide-nitride-oxide) (oxide/nitride/oxide) (silicon near oxide/silicon near nitride/silicon near oxide)) and (@ad<20030514 @rlad<20030514)) and (((insulat\$3 dielectric) near (layer film)) SOI (silicon near on near insulator)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/09/21 13:53 |